

IN THE CLAIMS:

This listing of claims will replace all prior versions, and listings, of claims in the application:

1-6. (Canceled)

7. (Currently Amended) A method of manufacturing a semiconductor device, comprising the steps of:

changing an optical path length of at least one laser beam of a plurality of laser beams from a plurality of pulse oscillation type solid lasers as light sources; and

synthesizing the plurality of laser beams ~~to irradiate a semiconductor film.~~ ; and

reflecting the synthesized laser beam by at least one mirror in order to irradiate a semiconductor film.

8. (Original) A method according to claim 7, wherein an output time of the laser beam is 1 to 50 ns.

9. (Original) A method according to claim 7, wherein the pulse oscillation type solid laser is one selected from the group consisting of a YAG laser, a YVO₄ laser, a YLF laser, a YAlO₃ laser, a glass laser, a ruby laser, an alexandrite laser, and a Ti:sapphire laser.

10. (Original) A method according to claim 7, wherein the semiconductor film is a film containing silicon.

11. (Currently Amended) A method according to claim 7, wherein said semiconductor device ~~comprises~~ is incorporated in a display part of at least one electric equipment selected from the group consisting of a video camera, ~~a digital camera~~, a digital camera, a projector, a head-mounted display, a goggle type display, a car navigation system, a car stereo, a personal computer, a mobile information terminal, a mobile computer, a mobile telephone, and an electronic book.

12. (Currently Amended) A method of manufacturing a semiconductor device, comprising the steps of:

oscillating a first laser beam from at least one pulse oscillation type solid laser of a plurality of pulse oscillation type solid lasers;

oscillating a second laser beam from another pulse oscillation type solid laser; ~~and~~

synthesizing the first laser beam and the second laser beam ~~to irradiate a semiconductor film.~~
; and

reflecting the synthesized laser beam by at least one mirror in order to irradiate a semiconductor film.

13. (Original) A method according to claim 12, wherein an output time of the first laser beam or the second laser beam is 1 to 50 ns.

14. (Original) A method according to claim 12, wherein the pulse oscillation type solid laser is one selected from the group consisting of a YAG laser, a YVO4 laser, a YLF laser, a YAlO3 laser, a glass laser, a ruby laser, an alexandrite laser, and a Ti:sapphire laser.

15. (Original) A method according to claim 12, wherein the semiconductor film is a film containing silicon.

16. (Currently Amended) A method according to claim 12, wherein said semiconductor device ~~comprises~~ is incorporated in a display part of at least one electric equipment selected from the group consisting of a video camera, ~~a digital camera~~, a digital camera, a projector, a head-mounted display, a goggle type display, a car navigation system, a car stereo, a personal computer, a mobile information terminal, a mobile computer, a mobile telephone, and an electronic book.

17. (Currently Amended) A method of manufacturing a semiconductor device, comprising the steps of:

oscillating a first laser beam from at least one pulse oscillation type solid laser of a plurality of pulse oscillation type solid lasers;

oscillating a second laser beam from another pulse oscillation type solid laser;

changing an optical path length of at least one of the first laser beam and the second laser beam; and

synthesizing the first laser beam and the second laser beam to ~~irradiate a semiconductor film~~;
and

reflecting the synthesized laser beam by at least one mirror in order to irradiate a semiconductor film.

18. (Original) A method according to claim 17, wherein an output time of the first laser beam or the second laser beam is 1 to 50 ns.

19. (Original) A method according to claim 17, wherein the pulse oscillation type solid laser is one selected from the group consisting of a YAG laser, a YVO4 laser, a YLF laser, a YAlO3 laser, a glass laser, a ruby laser, an alexandrite laser, and a Ti:sapphire laser.

20. (Original) A method according to claim 17, wherein the semiconductor film is a film containing silicon.

21. (Currently Amended) A method according to claim 17, wherein said semiconductor device ~~comprises~~ is incorporated in a display part of at least one electric equipment selected from the group consisting of a video camera, ~~a digital camera~~, a digital camera, a projector, a head-mounted display, a goggle type display, a car navigation system, a car stereo, a personal computer, a mobile information terminal, a mobile computer, a mobile telephone, and an electronic book.

22. (New) A method of manufacturing a semiconductor device, comprising the steps of:
changing an optical path length of at least one laser beam of a plurality of laser beams from a plurality of pulse oscillation type solid lasers as light sources;
synthesizing the plurality of laser beams; and
forming the synthesized laser beam into a linear shape in order to irradiate a semiconductor film.

23. (New) A method according to claim 22, wherein an output time of the laser beam is 1 to 50 ns.

24. (New) A method according to claim 22, wherein the pulse oscillation type solid laser is one selected from the group consisting of a YAG laser, a YVO4 laser, a YLF laser, a YAlO3 laser, a glass laser, a ruby laser, an alexandrite laser, and a Ti:sapphire laser.

25. (New) A method according to claim 22, wherein the semiconductor film is a film containing silicon.

26. (New) A method according to claim 22, wherein said semiconductor device is incorporated in a display part of at least one electric equipment selected from the group consisting of a video camera, a digital camera, a projector, a head-mounted display, a goggle type display, a car navigation system, a car stereo, a personal computer, a mobile information terminal, a mobile computer, a mobile telephone, and an electronic book.

27. (New) A method of manufacturing a semiconductor device, comprising the steps of:
changing an optical path length of at least one laser beam of a plurality of laser beams from a plurality of pulse oscillation type solid lasers as light sources;
synthesizing the plurality of laser beams;
dividing the synthesized laser beam into a plurality of laser beams;
changing an optical path length of at least one laser beam of the plurality of laser beams; and
synthesizing the plurality of laser beams to irradiate a semiconductor film.

28. (New) A method according to claim 27, wherein an output time of the laser beam is 1 to

50 ns.

29. (New) A method according to claim 27, wherein the pulse oscillation type solid laser is one selected from the group consisting of a YAG laser, a YVO4 laser, a YLF laser, a YAlO3 laser, a glass laser, a ruby laser, an alexandrite laser, and a Ti:sapphire laser.

30. (New) A method according to claim 27, wherein the semiconductor film is a film containing silicon.

31. (New) A method according to claim 27, wherein said semiconductor device is incorporated in a display part of at least one electric equipment selected from the group consisting of a video camera, a digital camera, a projector, a head-mounted display, a goggle type display, a car navigation system, a car stereo, a personal computer, a mobile information terminal, a mobile computer, a mobile telephone, and an electronic book.